

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claims 1-11 (canceled)

Claim 12 (currently amended): A method of forming a semiconductor device, comprising:

forming a drain region within a semiconductor substrate;

forming a field oxide layer with a first edge disposed outwardly from the drain region; and

forming a floating ring structure with a second edge disposed inwardly from at least a portion of the field oxide layer wherein said first edge of said field oxide is aligned with said second edge of said floating ring structure; and

wherein the floating ring structure comprises a first dopant type that is substantially complimentary to a second dopant type used to form the drain region.

Claim 13 (original): The method of Claim 12, wherein the first dopant type comprises primarily a negative-type dopant and the second dopant type comprises primarily a positive-type dopant.

Claim 14 (original): The method of Claim 12, wherein the first dopant type comprises primarily a positive-type dopant and the second dopant type comprises primarily a negative-type dopant.

Claim 15 (original): The method of Claim 12, wherein forming the field oxide layer comprises a technique selected from a group consisting of local oxidation of silicon and shallow trench isolation.

Claim 16 (canceled)

Claim 17 (original): The method of Claim 12, wherein the floating ring structure is aligned within two levels of misalignment.

Claim 18 (original): The method of Claim 12, wherein the floating ring structure is formed substantially simultaneously with a channel region of the semiconductor device.

Claim 19 (original): The method of Claim 12, further comprising:

forming a backgate region within the semiconductor substrate; and

forming a channel region within the backgate region of the semiconductor substrate, wherein the channel region comprises a substantially similar dopant type as the floating ring structure, and wherein forming the channel region comprises performing a chain implant.

Claim 20 (canceled)